

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
150V	35mΩ @ V <sub>GS</sub> = 10V	46A

## Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

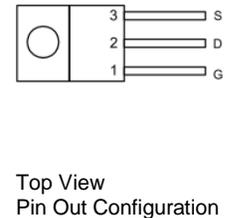
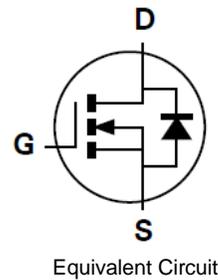
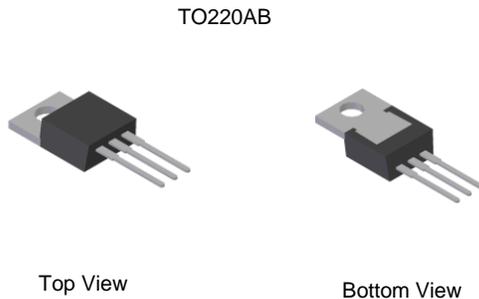
- Power Management Functions
- DC-DC Converters
- Backlighting

## Features and Benefits

- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> – Minimizes Power Losses
- Low Q<sub>G</sub> – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

- Package: TO220AB
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (Ⓜ)
- Weight: 2.24 grams (Approximate)

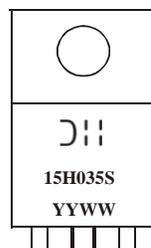


## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMT15H035SCT	TO220AB	50pcs	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



Ⓜ = Manufacturer's Marking  
 15H035S = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 21 = 2021)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	150	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	I <sub>D</sub>	T <sub>C</sub> = +25°C	46
		T <sub>C</sub> = +70°C	37
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	184	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	46	A
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	184	A
Avalanche Current, L = 1mH (Note 8)	I <sub>AS</sub>	17	A
Avalanche Energy, L = 1mH (Note 8)	E <sub>AS</sub>	144.5	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	55	°C/W
	Steady State		
Total Power Dissipation (Note 5)	P <sub>D</sub>	166	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	0.75	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	2.8	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	22	35	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1600	—	pF	V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	160	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4.2	—		
Gate Resistance	R <sub>g</sub>	—	0.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	25	—	nC	V <sub>DS</sub> = 75V, I <sub>D</sub> = 4.1A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	9	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	6	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	16.6	—	ns	V <sub>DS</sub> = 75V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.1A, R <sub>g</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	15.3	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	26.5	—		
Turn-Off Fall Time	t <sub>F</sub>	—	13.7	—		
Reverse Recovery Time	t <sub>RR</sub>	—	53	—	ns	I <sub>F</sub> = 4.1A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	47	—	nC	

- Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

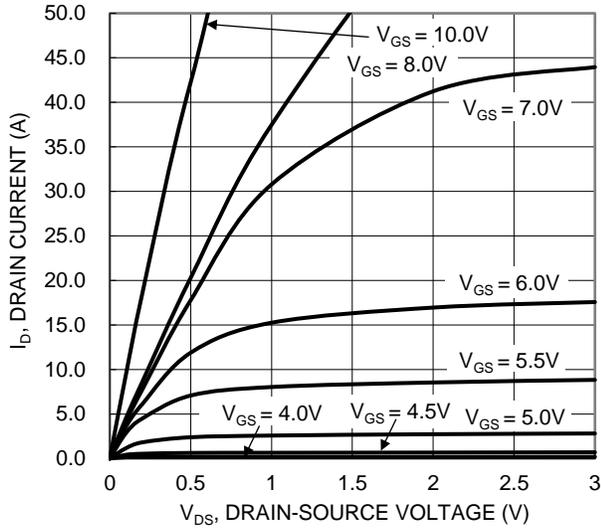


Figure 1. Typical Output Characteristic

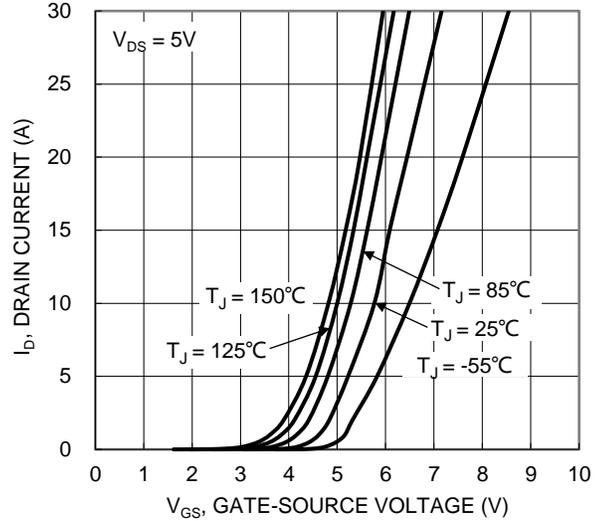


Figure 2. Typical Transfer Characteristic

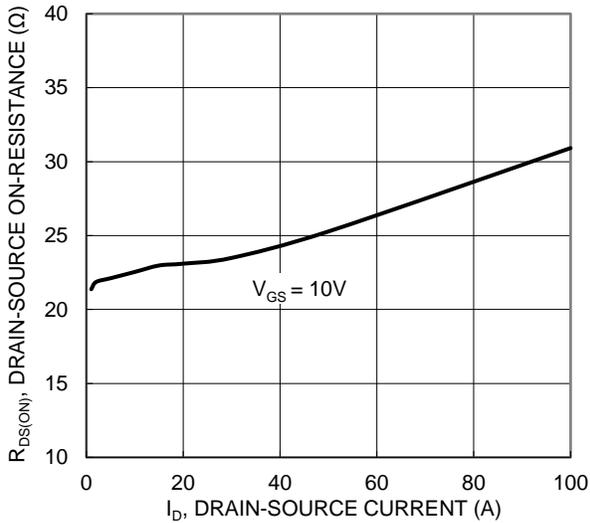


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

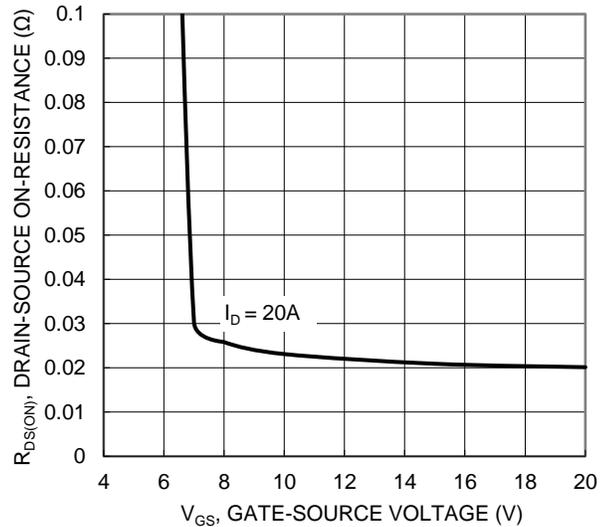


Figure 4. Typical Transfer Characteristic

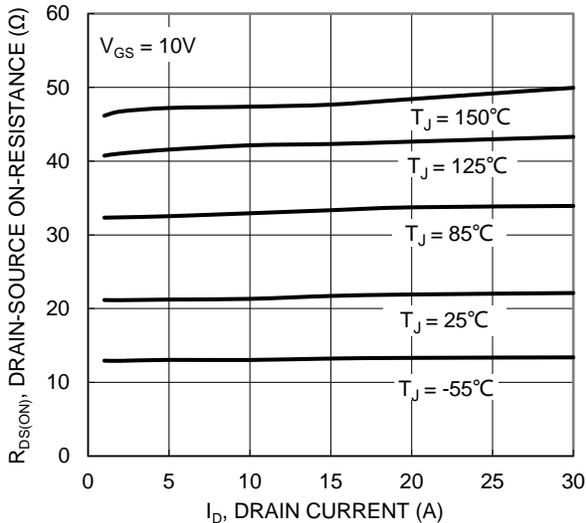


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

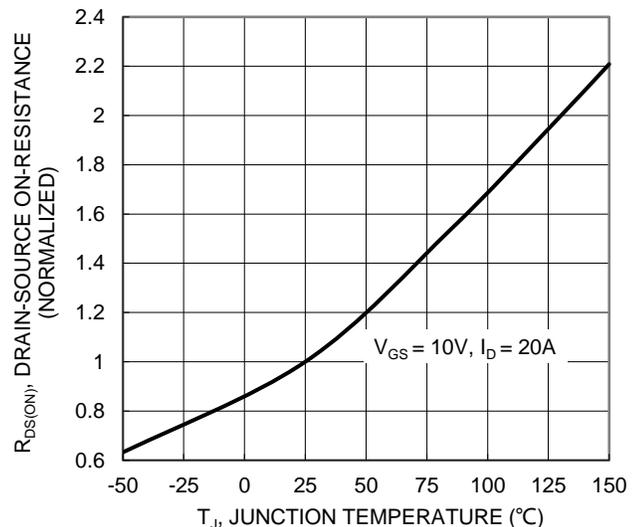


Figure 6. On-Resistance Variation with Junction Temperature

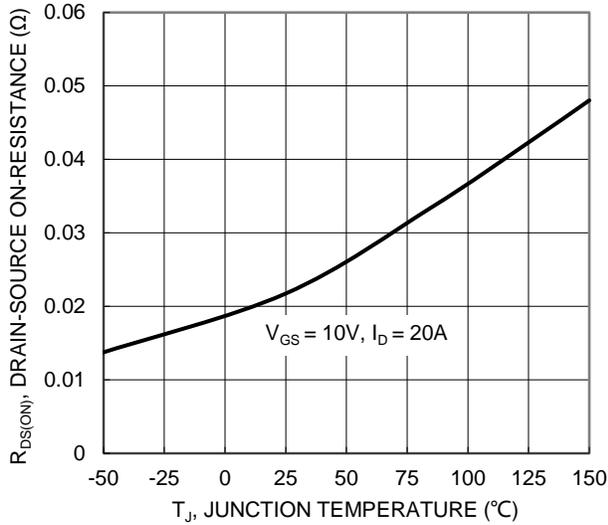


Figure 7. On-Resistance Variation with Junction Temperature

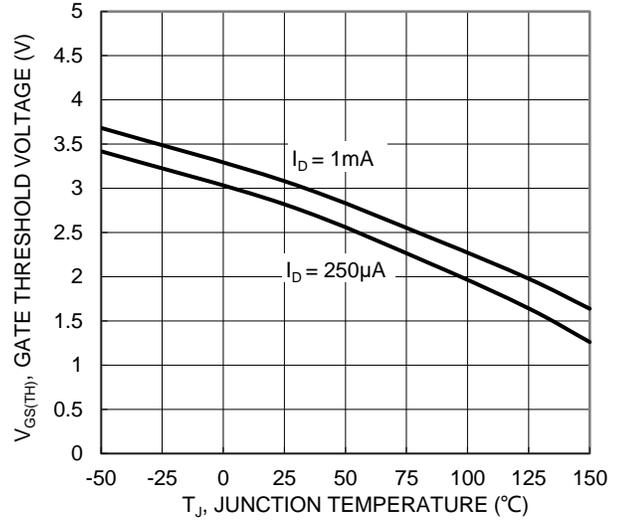


Figure 8. Gate Threshold Variation vs. Junction Temperature

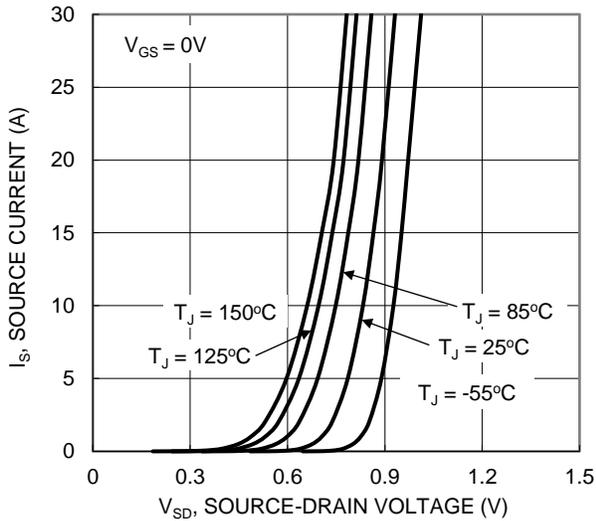


Figure 9. Diode Forward Voltage vs. Current

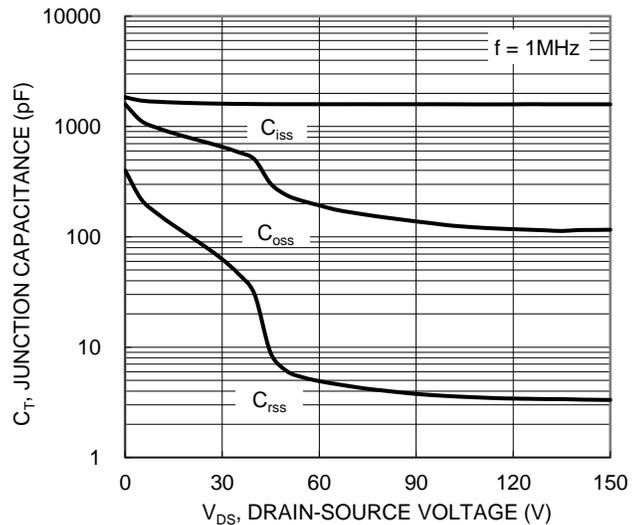


Figure 10. Typical Junction Capacitance

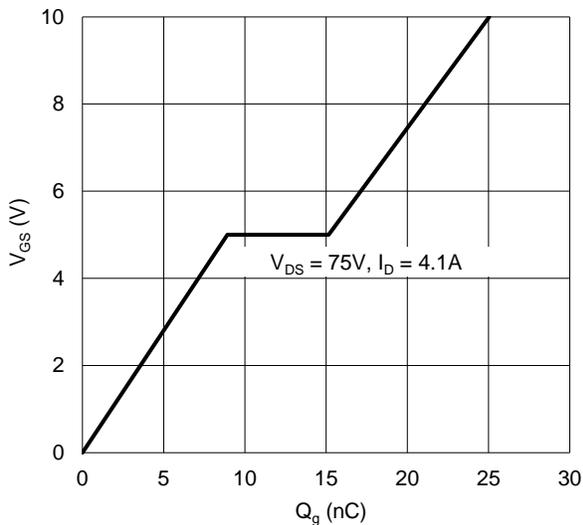


Figure 11. Gate Charge

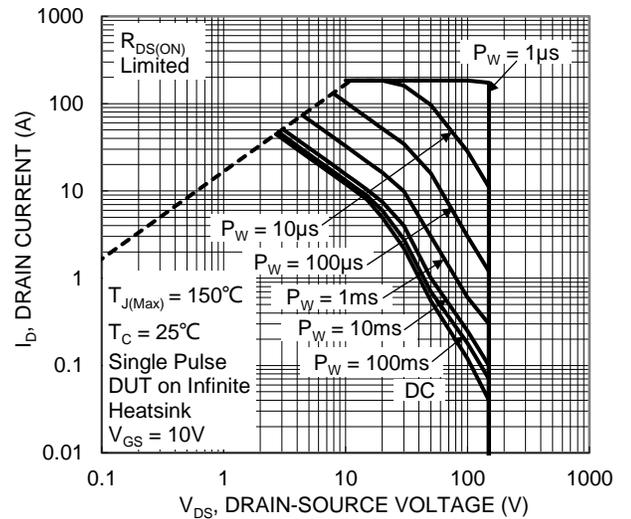


Figure 12. SOA, Safe Operation Area

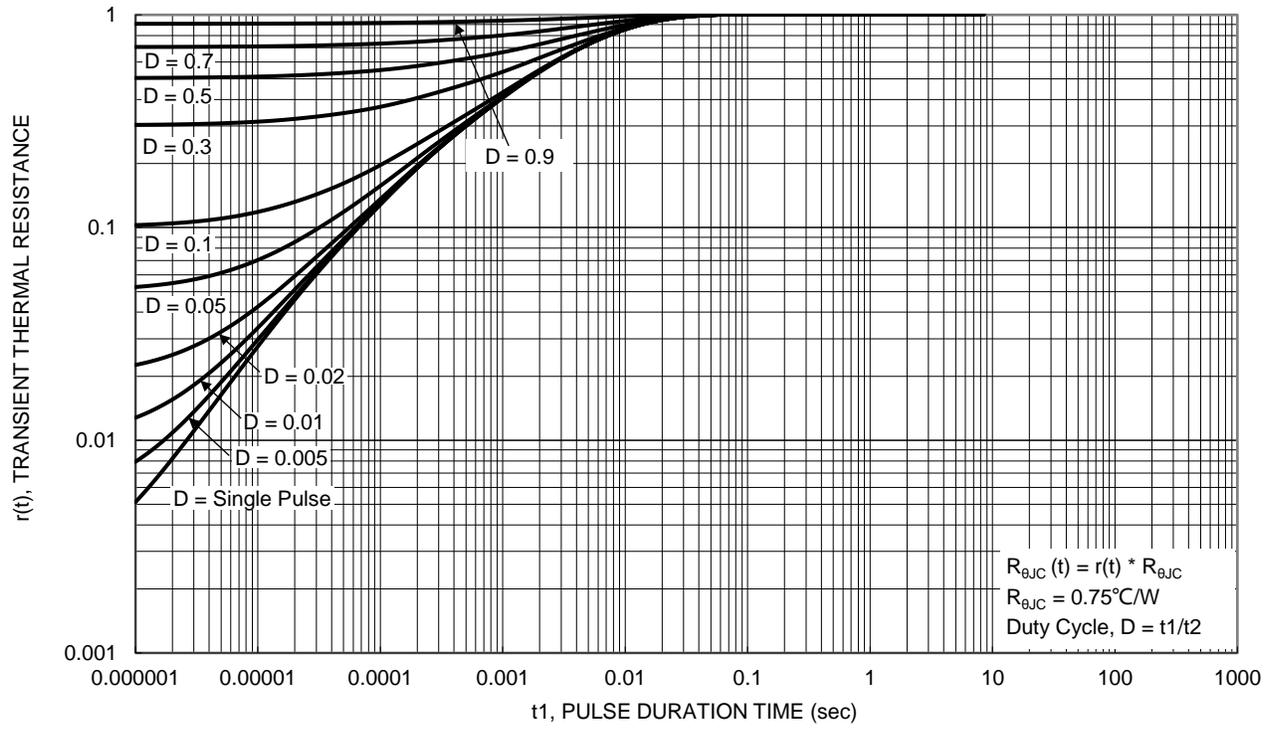
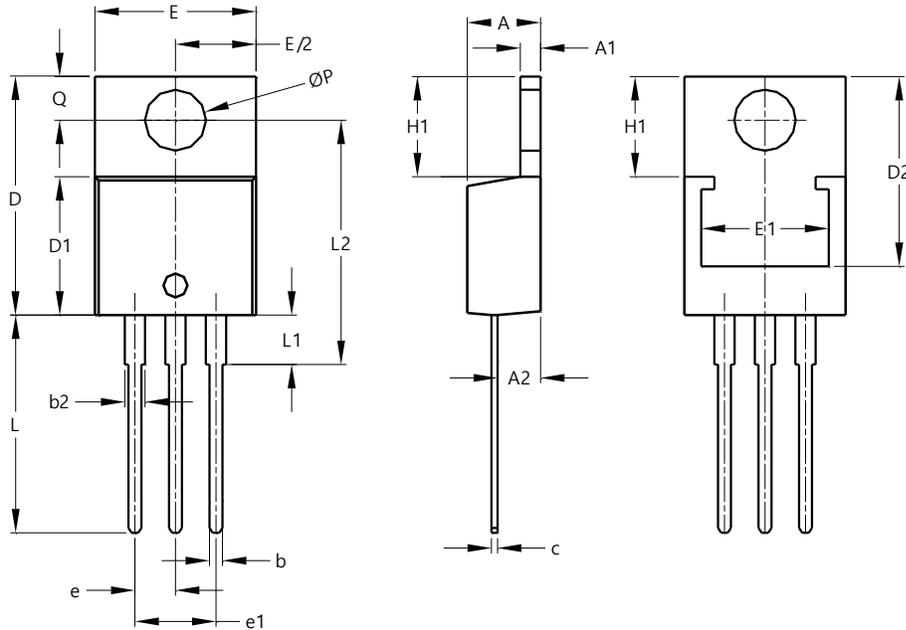


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO220AB**



TO220AB			
Dim	Min	Max	Typ
A	3.56	4.82	-
A1	0.51	1.39	-
A2	2.04	2.92	-
b	0.39	1.01	0.81
b2	1.15	1.77	1.24
c	0.356	0.61	-
D	14.22	16.51	-
D1	8.39	9.01	-
D2	11.45	12.87	-
e	-	-	2.54
e1	-	-	5.08
E	9.66	10.66	-
E1	6.86	8.89	-
H1	5.85	6.85	-
L	12.70	14.73	-
L1	-	4.42	-
L2	15.80	17.51	16.00
P	3.54	4.08	-
Q	2.54	3.42	-
<b>All Dimensions in mm</b>			

**Note:** For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance.

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